## **ABSTRACT**

1 Heat is applied to a conductive structure that includes 2 one or more vias, and the temperature at or near the point of 3 heat application is measured. The measured temperature indicates the integrity or the defectiveness of various features 4 5 (e.g. vias and/or traces) in the conductive structure, near the 6 point of heat application. Specifically, a higher temperature 7 measurement (as compared to a measurement in a reference 8 structure) indicates a reduced heat transfer from the point of 9 heat application, and therefore indicates a defect. The 10 reference structure can be in the same die as the conductive 11 structure (e.g. to provide a baseline) or outside the die but in the same wafer (e.g. in a test structure) or outside the wafer 12 13 (e.g. in a reference wafer), depending on the embodiment.